EXPRESS MAIL MAILING LABEL

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INFORMATION DISCLOSURE STATEMENT	APPLICANT: Fitzgerald
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	A192	5,571,373	11/05/1996	Krishna et al.			
	A193	5,633,202	05/27/1997	Brigham et al.			
	A194	5,710,450	01/20/1998	Chau et al.			
	A195	5,976,939	11/02/1999	Thompson et al.			
	A196	6,876,053	04/05/2005	Ma et al.			

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